
Augmented NDEF with ST25DV-I2C series Dynamic NFC Tags

Introduction

The purpose of this application note is to explain how a microcontroller can enhance the performance of ST25DV-I2C series Dynamic NFC Tags (hereinafter referred to as ST25DV-I2C), in particular how to provide augmented NDEF experience to end-users.

ST25DV-I2C devices (namely ST25DV04/16/64K and ST25DV04/16/64KC) embed EEPROMs with 4/16/64 Kbit densities.

Augmented NDEF stands for an NDEF (NFC data exchange format) message stored in an NFC Forum tag, whose content is dynamically modified by the tag to provide additional information.

NDEF messages are stored in the ST25DV-I2C and read by NFC Forum compatible devices. These messages contain information such as URI, text, images and Bluetooth® connection.

When reading the NDEF message, NFC Forum compatible smartphones automatically trigger specific actions, without the requirement of an external application, such as opening the web browser for an NDEF message containing a URL, or automatically performing Bluetooth pairing.

The content of an NDEF message in an NFC Forum tag is usually static. It is modified by an NFC Forum reader or a smartphone, but it does not automatically change on external events. It is interesting to dynamically update the content of an NDEF message upon external or internal events. For example, embed dynamic information in an URL to automatically redirect the user to a personalized web page, or embed sensors data into an SMS or e-mail to automatically send sensors' data when tapping the tag. These actions are performed without the requirement of an additional application thanks to Android™ and iOS native support of NDEF message reading.

Contents

1	Overview	5
2	Augmented NDEF content update	6
2.1	Automatic NDEF content update on phone detection	6
2.1.1	Arbitration between RF and I2C interfaces	6
2.1.2	NDEF detection and reading procedure in smartphones	7
2.1.3	Timing constraints for automatic NDEF content update	11
2.1.4	Battery-less automatic NDEF content update implementation	12
2.1.5	Battery powered automatic NDEF content update implementation	19
2.2	Periodical NDEF content update and update based on external events .	24
2.3	Configuration data considerations	25
3	Revision history	26

List of tables

Table 1. Possible cases of communication arbitration 7

Table 2. Tag memory content (ST25DV04K) 14

Table 3. Tag memory content (ST25DV04KC)..... 17

Table 4. Document revision history 26

List of figures

Figure 1.	Application board	5
Figure 2.	Phone 1 tag detection phase	8
Figure 3.	Phone 2 tag detection phase	8
Figure 4.	Phone 3 tag detection phase	9
Figure 5.	RF polling frequency (phone 3)	10
Figure 6.	Phone 2 NDEF read phase.	11
Figure 7.	Phone 1 NDEF read phase.	11
Figure 8.	Battery-less application example hardware setup	14
Figure 9.	Battery-less NDEF update capture with phone 1 (ST25DV04K)	16
Figure 10.	Battery-less NDEF update capture with phone 4 (ST25DV04K)	16
Figure 11.	Battery-less NDEF update example result on phone 4 (ST25DV04K)	17
Figure 12.	Battery-less NDEF update capture with phone 4 (ST25DV04KC)	18
Figure 13.	Battery powered NDEF update chronogram (1/2)	20
Figure 14.	Battery powered NDEF update chronogram (2/2)	20
Figure 15.	Battery powered NDEF update capture with phone 4 (NDEF update phase).	23
Figure 16.	Battery powered NDEF update capture with phone 4 (NDEF reading phase)	23
Figure 17.	Battery powered NDEF update example result on smartphone	24

1 Overview

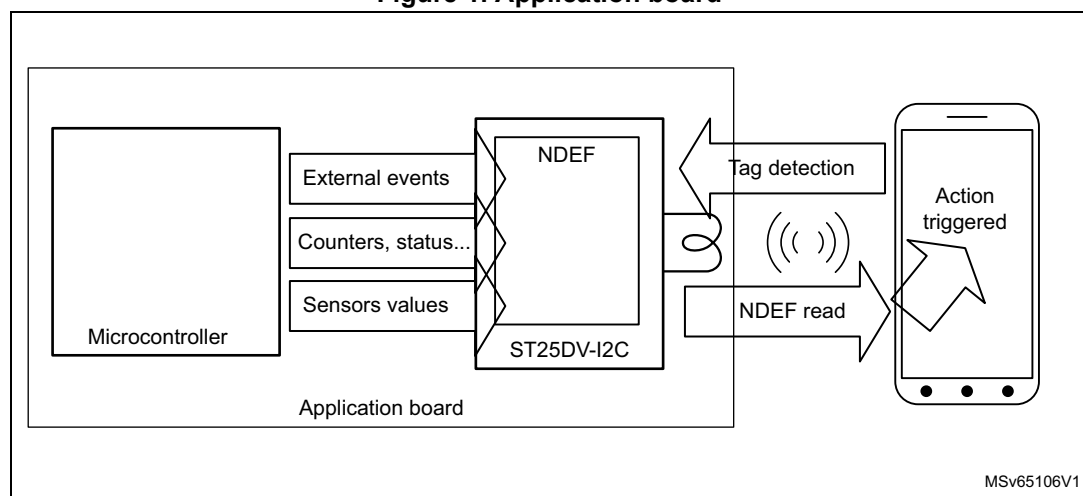
The EEPROM content is accessed by either a smartphone or an NFC Forum reader through its RF interface, and by a microcontroller through its wired I2C interface.

The NDEF message is stored in the user memory of the ST25DV-I2C.

When the smartphone is close enough to the ST25DV-I2C antenna, it detects the tag presence and starts reading the NDEF message stored in the ST25DV-I2C memory (see [Figure 1](#)).

The content of NDEF message is usually static, but the microcontroller updates the content of the NDEF message, either in background or dynamically when the phone is approached so that the NDEF message always contains dynamic data.

Figure 1. Application board



Several data append dynamically to the NDEF message, among them:

- Identification information (such as UID, signature)
- Tap counter
- Tamper status
- MAC (message authentication code)
- Sensors values (e.g. temperature, humidity, pressure, distance, voltage)
- GPS position
- Date and time
- Battery power level
- Diagnostic log

Thanks to the native support of NDEF message by Android and iOS-based smartphones, an action is automatically triggered on the phone while reading the NDEF message, such as opening a browser, sending an email or a text message, or opening an application.

2 Augmented NDEF content update

The NDEF message content is updated by the microcontroller in three phases:

Phase 1 and 2:

1. When the presence of a smartphone is detected, and before the smartphone starts to read the NDEF message
2. During NDEF read by the smartphone

Phase 3:

3. Any other time, when the smartphone does not try to read the NDEF message

The first two phases are “on-demand update” of the NDEF message. The content is updated “just in time” each time the smartphone tries to read the NDEF message.

The third one is asynchronous regarding the smartphone presence. It corresponds to a periodical update of the NDEF message, or to an update triggered by other external events (such as an interruption from a sensor).

The following sections focus on the “on demand update” method, since the asynchronous method does not imply specific techniques.

2.1 Automatic NDEF content update on phone detection

There are several advantages to update NDEF message content on phone detection: data are always fresh, and application can run battery-less (assuming power consumption is low enough to enable power through energy harvesting).

However, this is the most challenging method as it requires important timing constraints. Depending on the amount of data to update it may not be possible to implement it.

To understand the timing constraints, user has to first understand how arbitration between I2C and RF interface works in the ST25DV-I2C and how a smartphone detects the tag presence and reads the NDEF message.

2.1.1 Arbitration between RF and I2C interfaces

In the case of NDEF message update on phone detection, both the the microcontroller (through I2C interface) and the smartphone (through the RF interface) try to access the ST25DV-I2C. The microcontroller tries to write the EEPROM and the smartphone tries to read it.

Due to their nature, these two host controllers are not synchronized, which means that they try to access the ST25DV-I2C concurrently. To manage such situation, the ST25DV-I2C has built-in arbitration circuitry to handle concurrent communications from the RF and I2C sides.

The arbitration is based on the “first talked - first served” principle. It depends on whether the I²C and RF channels are in the busy state:

- ST25DV-I2C is in I²C busy state when decoding and executing an I²C command, and during the EEPROM programming time that follows a valid I2C write command.
- ST25DV-I2C is in RF busy state when decoding and executing an RF command.

When both interfaces are active, the ST25DV-I2C decodes and executes the first received command (see [Table 1](#)), which describes possible cases of communication arbitration.

Table 1. Possible cases of communication arbitration

Initial state event action	Event	Action
ST25DV-I2C is in the I ² C busy state: an I ² C command is being decoded or executed	RF command transmitted during an I ² C command	The RF command is not decoded ⁽¹⁾
ST25DV-I2C is in the RF busy state: an RF command is being decoded or executed	I ² C command transmitted during an RF command	The I ² C command is not decoded ⁽²⁾

1. RF commands inventory, stay quiet and addressed RF commands where UID (unique identifier) match receive no response. Other RF commands receive error code 0Fh.
2. I²C master receives a slave "No Ack" state on 9th bit of first data byte (that is, device select).

The main challenge for updating NDEF message on phone detection is to avoid having the smartphone sending RF requests when I2C is busy (as shown in the first row of [Table 1](#)). Ultimately, a smartphone receiving an error on an RF request (or no answer) usually aborts the NDEF reading procedure, This must be avoided.

2.1.2 NDEF detection and reading procedure in smartphones

On smartphones (and all NFC Forum compliant readers) NDEF message reading are separated in two main phases: tag detection and NDEF read.

Tag detection phase

During the tag detection phase, the smartphone first emits short 13.56 MHz unmodulated pulses to detect the presence of a 13.56 MHz sensitive object in the field.

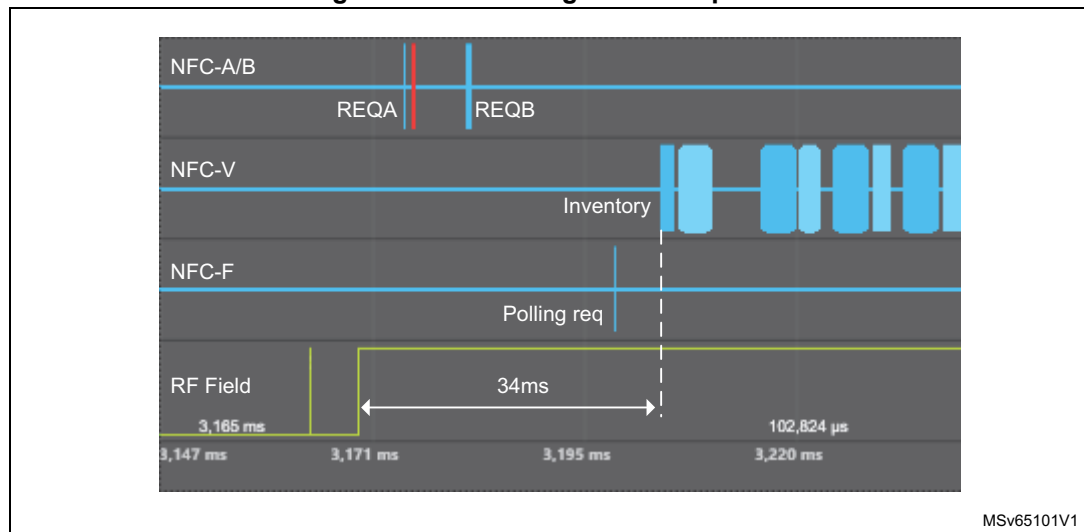
If a presence is detected, the smartphone starts to emit a continuous 13.56 MHz RF field and starts anti-collision procedure for all the NFC Forum technologies supported (this step is described in the 'activity' specification of the NFC Forum and is called technology detection activity).

Most smartphones (Android and iOS) support and poll for NFC Forum NFC-A, NFC-B, NFC-F and NFC-V technologies. Some smartphones also support and poll for ACM (active communication mode, in NFC-A or NFC-F or both).

The NFC-V detection and anti-collision is always performed last. This means that there is some delay between the rising of the RF field and the start of NFC-V anti-collision (inventory command). This delay is typically around 35 ms but may vary from one smartphone to another. It can be higher than 35 ms but cannot be less than 30 ms if the four NFC-A/B/F/V technologies are supported (as defined in NFC Forum specification).

[Figure 2](#), [Figure 3](#) and [Figure 4](#) show the tag detection phase of three smartphones embedding different operating systems captured with an RF spy analyzer. Commands sent by the smartphone for each NFC technology and RF field status are recorded by the RF spy.

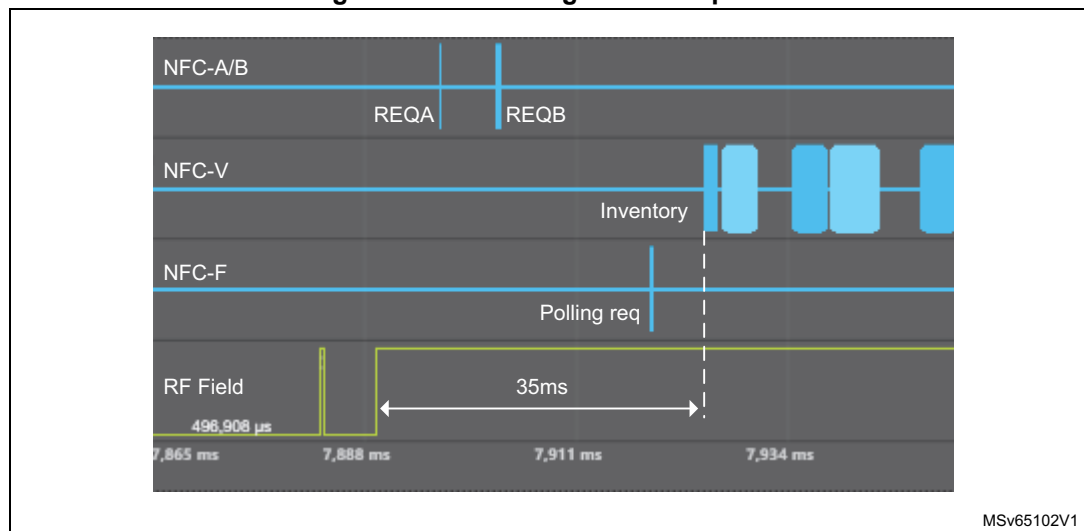
Figure 2. Phone 1 tag detection phase



Phone 1 detects presence of a tag and then tries to detect NFC technologies:

- The phone first sends a very short pulse at 13.56 MHz unmodulated for about 40 μs.
- Then the RF field is off for 5.4 ms.
- After this pause, the NFC technology detection starts: first NFC-A, then NFC-B, NFC-F and finally, 34 ms after the RF field rising, NFC-V technology.
- The first NFC-V command sent is an inventory command (anti-collision).

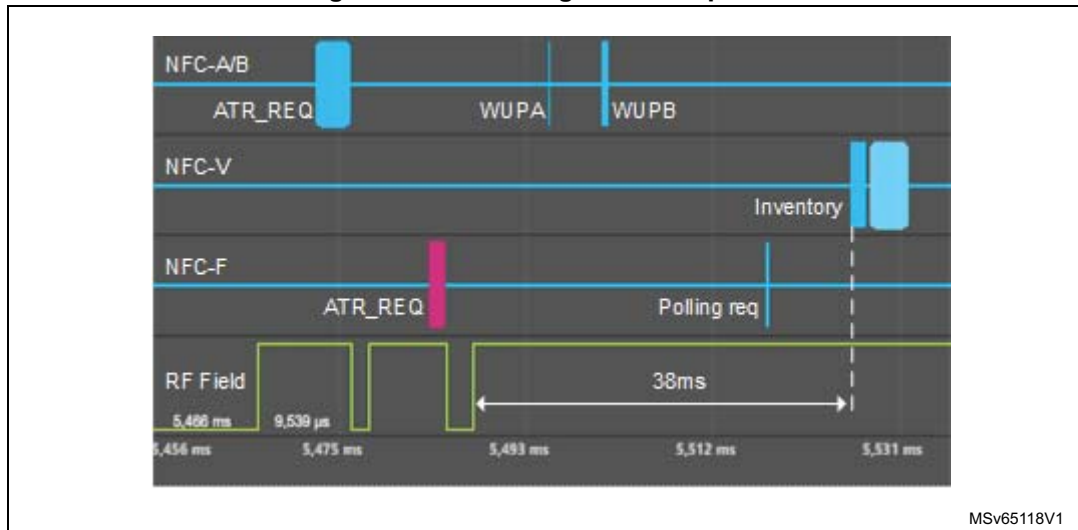
Figure 3. Phone 2 tag detection phase



Phone 2 tag detection phase is very similar to that of phone 1. Timings are slightly different:

1. First short 13.56 MHz unmodulated pulse duration is about 320 μs.
2. Pause before NFC technology detection is about 5.7 ms.
3. NFC-V anti-collision starts 35 ms after the RF field rising.

Figure 4. Phone 3 tag detection phase



Phone 3 tag detection phase starts with two pulse of modulated 13.56 MHz RF field, each followed by a pause, to detect NFC peer-to-peer devices (ACM). After this, procedure is identical to that seen for phone 1 and phone 2. Timings are:

1. 13.56 MHz pulse: 9.5 ms, then 1.8 ms pause
2. 13.56 MHz pulse: 7.8 ms, then 2.78 ms pause
3. NFC tag detection with NFC-V anti-collision 38 ms after the RF field rising.

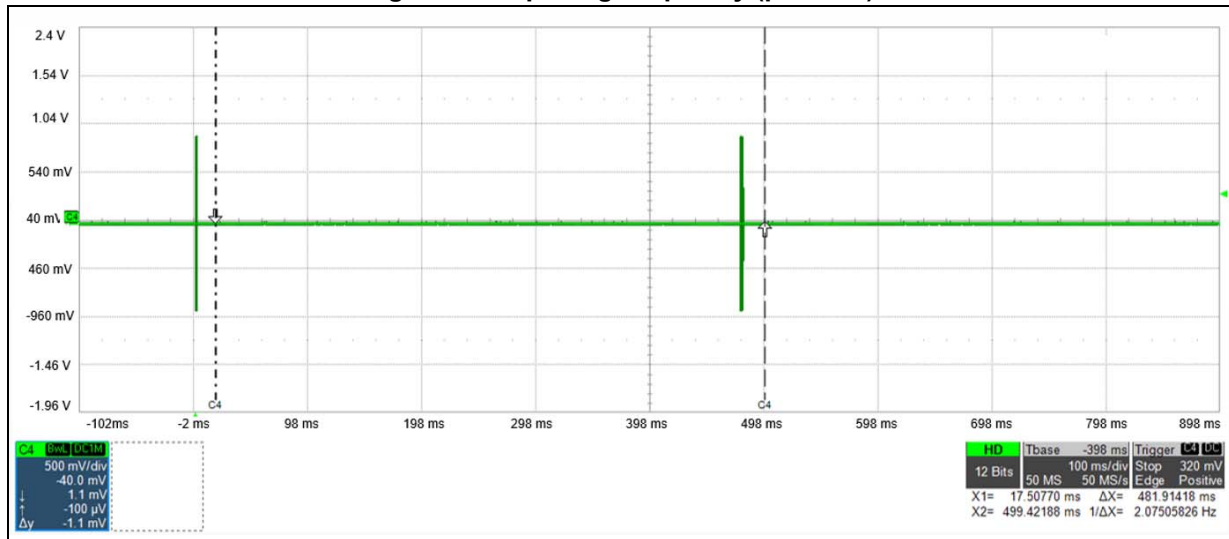
These three smartphones summarize what typically happens, whatever the embedded OS.

The 30 ms minimum delay before start of NFC-V anti-collision allows the microcontroller to update the NDEF message content in the ST25DV-I2C memory. ST25DV-I2C can provide power to boot the microcontroller through energy harvesting as soon as RF field is rising, and the microcontroller then has 30 ms before the first NFC-V commands (inventory) to update the NDEF message through I2C. This method is detailed in [Section 2.1.4](#).

After NFC-V anti-collision phase, if no tag has been found (no answer to the inventory command), the smartphone stops emitting the RF field to save battery. The inventory command duration is 2.2 ms.

Then, the smartphone starts a new polling phase later, with a polling frequency usually around 500 ms, as shown in [Figure 5](#).

Figure 5. RF polling frequency (phone 3)



If the required time to update the NDEF message exceeds 30 ms, the microcontroller enables the use of the polling phase by updating the NDEF message content on detection of a first polling phase and let the tag answer to the smartphone only on a later polling phase. The GPO_FIELD_CHANGE interruption of ST25DV-I2C detects the RF field. The time allocated to update the NDEF message is then only limited by the response time perceived by the user. However, as the RF field is not present between each polling phase, it is not possible to use energy harvesting to power the microcontroller, therefore battery or permanent power is required. This method is detailed in [Section 2.1.5](#).

NDEF read phase

After NFC-V anti-collision is performed, the smartphone starts the NDEF read procedure. This procedure is specified by NFC Forum for Type 5 tags.

The procedure starts quickly after the inventory command with the read of the CC file: the phone sends a read single block command to read the first 4 (or 8 bytes) of the tag. Then the phone sends several read single block commands or read multiple block commands to read the NDEF message itself (starting quickly after CC file).

Android smartphones add some ISO15693 commands between the inventory of the tag detection procedure and the NDEF read procedure: get system information and get multiple block security status.

In NFC Forum NFC-V technology, the minimum timing between two consecutive RF commands (time between end of the response and start of a new request) is 309 μ s. In practice, delay between two RF commands in smartphones is larger, typical values are between 1.5 and 5 ms. This delay is usually too short to allow any I2C write access to the ST25DV-I2C EEPROM. Updating the NDEF message content during NDEF read by the smartphone is not a valid option. In fact, any I2C request not terminated before start of a new RF command can cause an RF error answer and immediate stop of the NDEF reading process by the smartphone.

Figure 6. Phone 2 NDEF read phase

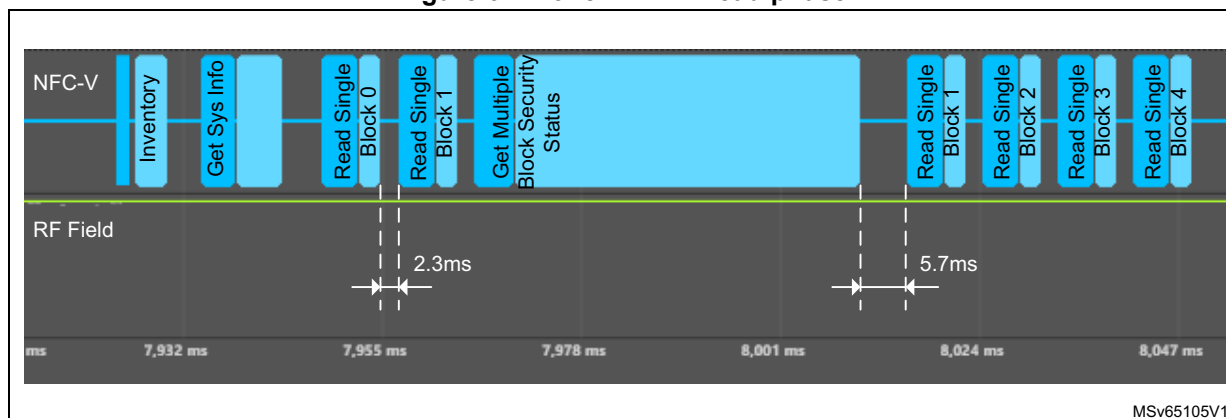
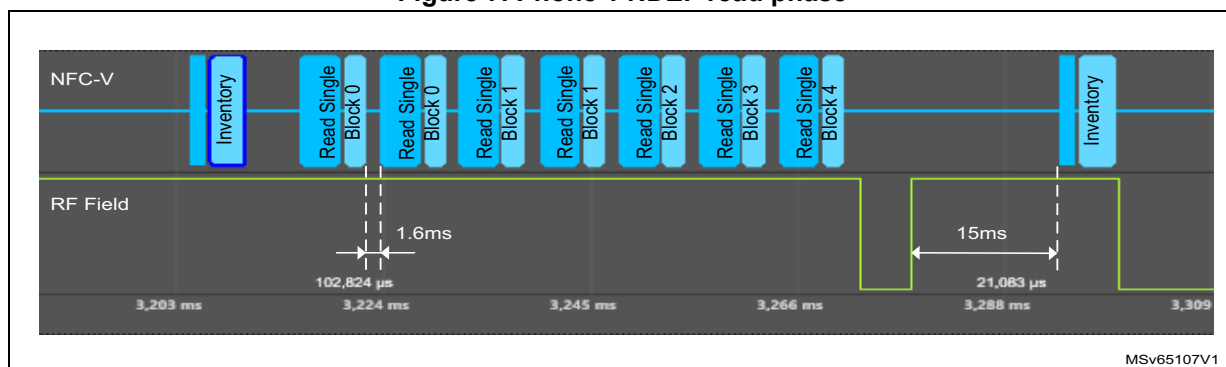


Figure 7. Phone 1 NDEF read phase



Phone 1 stops emitting the RF field after end of NDEF read, and then regularly re-activates the RF and sends an inventory command to check that the tag is still present.

2.1.3 Timing constraints for automatic NDEF content update

The constraint is to avoid any RF command fail, to avoid abortion from the smartphone. This means no RF command received during execution of an I2C command (including EEPROM programming time).

To update the NDEF message, the microcontroller has to write data into ST25DV-I2C EEPROM. The ST25DV-I2C programming time is 5 ms per block of 4 bytes (assuming all bytes belonging to a same row, aka page).

As described in [NDEF read phase](#), the delay between two consecutive RF commands during the NDEF read phase is less than 5 ms, it is therefore not possible to write data from I2C in ST25DV-I2C EEPROM during this phase without causing arbitration conflict with RF commands.

Therefore, to avoid any collision between RF and I2C, the NDEF update must be completed by the microcontroller between RF field rise and start of anti-collision (first inventory command), which is usually at least 30 ms for most smartphones.

NDEF update timing is separated into three phases:

1. Microcontroller wakes-up or boots
2. Microcontroller may read data into ST25DV-I2C (typically a counter value) or into external devices (typically sensors)
3. Microcontroller writes into ST25DV-I2C EEPROM (NDEF content update)

The microcontroller wakeup and boot phase is not detailed in this application note as it differs from one microcontroller to another.

The data read phase speed essentially depends on I2C bus frequency and if external devices required being accessed (that is, sensors with long conversion time).

The ST25DV-I2C memory update speed is mainly dependent on EEPROM programming time. To calculate the duration of an I2C write it is possible to split the I2C write command in two parts: the I2C bytes transmitted on the bus and the EEPROM programming phase that starts right after the STOP condition:

- I2C write command duration = $(3 + \text{number of bytes to write}) / (9 * \text{I2C clock period})$
- EEPROM programming duration = $5 * 10^{-3} * (\text{number of pages to program})$
- Total duration of the I2C write = I2C write command duration + EEPROM programming duration

EEPROM pages of ST25DVxxK devices are 16-byte long. Data located on the same page share the address bits b16-b2. In terms of duration, programming one byte is equivalent to programming one page, programming five bytes is equivalent to programming two pages.

For example, for ST25DV04K, with an I2C clock of 400 KHz, it is possible to write 16 bytes starting at address 000Ch in 20 ms. If starting at address 000Bh, or if writing 17 bytes starting at address 000Ch, the operation takes 25 ms.

In ST25DVxxKC, EEPROM pages are 16-byte long. Data located on the same page share the address bits b16-b4. In terms of duration, programming five bytes is equivalent to programming one page, programming 17 bytes is equivalent to programming two pages.

For example, in ST25DV04KC with an I2C clock of 1MHz, it is possible to write 16 bytes starting at address 0010h in 5 ms. If starting at address 0011h, or if writing 17 bytes starting at address 0010h, the operation takes 10 ms. Therefore, the possible amount of data updated in the NDEF message is limited and special care must be taken on the start address and the resulting number of pages to program.

If the length of data to be updated is larger than 4 bytes, ST25DVxxKC devices should be preferred over ST25DVxxK.

2.1.4 Battery-less automatic NDEF content update implementation

As described in previous sections, it is possible to make a battery-less application using a ST25DV-I2C dynamic tag and a microcontroller to create an augmented NDEF application.

The application must update the NDEF message as soon as the smartphone starts to provide RF field, and in less than 30 ms to allow correct reading of the NDEF message by the smartphone.

In principle, this augmented NDEF application:

- Behaves as a standard NFC tag
- Boots the microcontroller when RF field is rising
- Makes use of energy harvesting to power the microcontroller and possibly other on-board external devices

- Reads data in ST25DV-I2C and possibly other on-board external devices
- Writes data into the ST25DV-I2C memory to update NDEF message content
- Does all this before the first NFC-V command (in less than 30 ms)

In order to achieve this, the prerequisites are:

1. The initial NDEF message has been previously programmed into ST25DV-I2C memory.
2. The ST25DV-I2C has been configured with EH enabled at boot (EH_MODE configuration register=00h).
3. Minimal number of components and components with low power consumption are used.

To reach the 30 ms max timing, all phases must be time-optimized: capacitor charging when EH start providing current, MCU boot time, data reading and data writing. Special attention is required to avoid tearing issues.

During a write of data into EEPROM, it is possible that the RF field gets lost (that is, if smartphone is removed). To avoid data corruption in that case, an anti-tearing mechanism must be put in place.

A simple solution is to finish the NDEF update by writing a counter, and to protect only this counter from tearing. The validity of NDEF data is guaranteed if the counter value is higher than previous value (counter incremented).

In order to protect the counter from tearing, the energy stored in capacitors is used. As explained in [Section 2.1.3](#), the EEPROM programming starts only after the stop condition of an I2C write command. During the EEPROM programming, only the ST25DV-I2C requires being powered through its V_{CC} pin, since the microcontroller does not require anymore to provide I2C clock or any other signal. By only keeping the ST25DV-I2C powered after the stop condition of the last I2C write (counter update), the power consumption is minimal and the ST25DV-I2C is powered by capacitor discharge if RF field is removed. This provides an anti-tearing for the counter update.

Capacitor discharge at constant current is calculated as $C = I * dt / dV$. Assuming $I = 350 \mu A$ (max value at 3.3 V, 125 °C), $dV = 3 V - 1.8 V$ (3 V is the typical EH output value and 1.8 V is the minimum operating voltage for ST25DV-I2C), and $dt = 5 ms$ (typical page write time), the minimum C value needed to power the ST25DV-I2C to write a page is 1.46 μF . If counter is more than one page (4 bytes for the ST25DVxxK and 16 bytes for the ST25DVxxKC), dt must be augmented by steps of 5 ms per page.

The capacitor value must be balanced with capacitor charging time in order not to have a too long charging time to reach the 1.8 V when EH power is starting power delivery. The capacitor charging time must be taken into consideration when trying to keep the total NDEF update timing under 30 ms.

Example of battery-less automatic NDEF content update with ST25DV04K

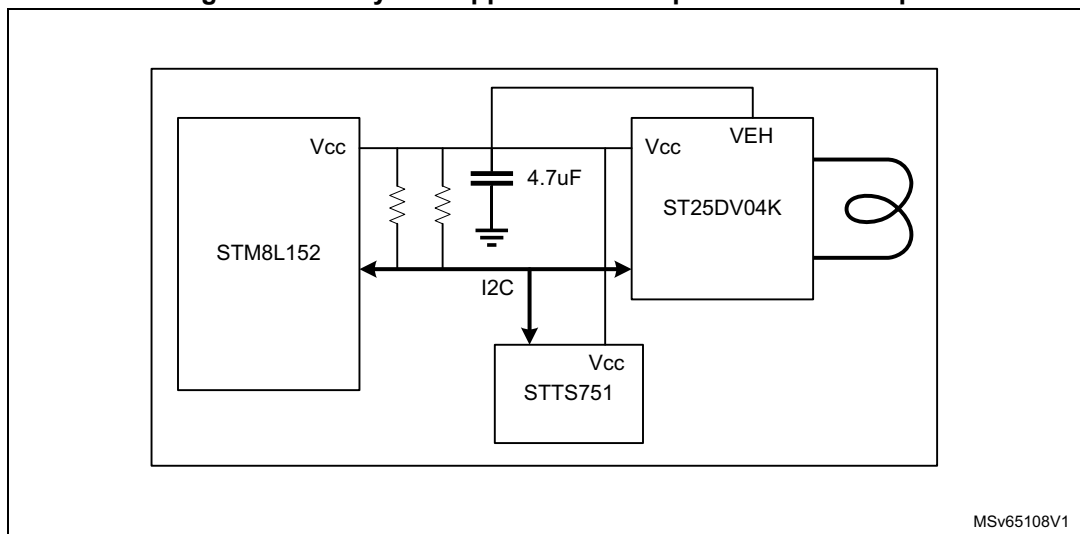
In this example the augmented NDEF tag provides a NDEF message containing a URL. The end of the URL is automatically completed with a temperature value read in a sensor and a tap counter incremented at each NDEF read.

Hardware setup:

- ST25DV04K dynamic tag, with NDEF message preloaded and EH enabled at boot
- STM8L152 ultra low power MCU
- STTS751 low power, fast conversion time, temperature sensor

- 2 x 4.7 μ F capacitors (plus 10 nF and 100 nF capacitors for device decoupling)

Figure 8. Battery-less application example hardware setup



The NDEF message is a URL type (example.com/temp=0000/tapcounter=0000) containing the following data:

- temperature value and tap counter value addresses are aligned with EEPROM pages and are only 4-byte long, to improve programming speed (5 ms for each)
- temperature and tap counter are written in ASCII format in the NDEF message
- tap counter on four characters is enough as it provides 10000 values if decimal is used, 65536 values if hexadecimal is used and 1.6×10^6 values if all alphanumeric values are used.

Table 2. Tag memory content (ST25DV04K)

Byte address	Byte value	ASCII	Comment
0000	E1 40 40 00	á@@.	CCFile
0004	03 2A D1 01	.*Ñ.	NDEF TLV
0008	26 55 01 65	&U.e	URL value
000C	78 61 6D 70	xamp	-
0010	6C 65 2E 63	le.c	-
0014	6F 6D 2F 74	om/t	-
0018	65 6D 70 3D	emp=	-
001C	30 30 30 30	0000	Temperature value
0020	2F 74 61 70	/tap	-
0024	63 6F 75 6E	coun	-
0028	74 65 72 3D	ter=	-
002C	30 30 30 30	0000	Tap counter value
0030	FE 00 00 00	p...	TLV terminator

Sample code executed by the microcontroller (with ST25DV04K):

```
/* initialize I2C bus and clocks */
I2C_Init();
/* Read I2C sensor to get current temperature */
GetOneTemperature (&data_sensor);
/* update temperature value in NDEF message */
ConvertTempToAscii(data_sensor, data_char);
I2C_WriteOnePage(ST25DV_ADDRESS_USER, temperature_addr, data_char);
/* poll for end of EEPROM programming (~5ms) */
while( I2C_Poll(ST25DV_ADDRESS_USER) );
/* read current tap counter in tag's EEPROM */
I2C_ReadBuffer(ST25DV _ADDRESS_USER, tapcounter_addr, 4, data_char);
/* increment tap counter and update value in NDEF message */
IncrementTapCounterAscii(data_char);
I2C_WriteOnePage(ST25DV_ADDRESS_USER, tapcounter_addr, data_char);
/* immediately stop MCU to reduce power consumption */
halt();
```

The initialization phase is kept minimal to shorten boot time. After finishing I2C write (tap counter), the microcontroller is set in halt mode to minimize power consumption (STTS751 is already in minimal power mode) so that all energy stored in capacitors is available to ST25DV-I2C in case of RF field off (anti-tearing of tap counter update).

[Figure 9](#) and [Figure 10](#) are oscilloscope screenshots showing the NDEF update in action on phone 1 and phone 4.

Figure 9. Battery-less NDEF update capture with phone 1 (ST25DV04K)

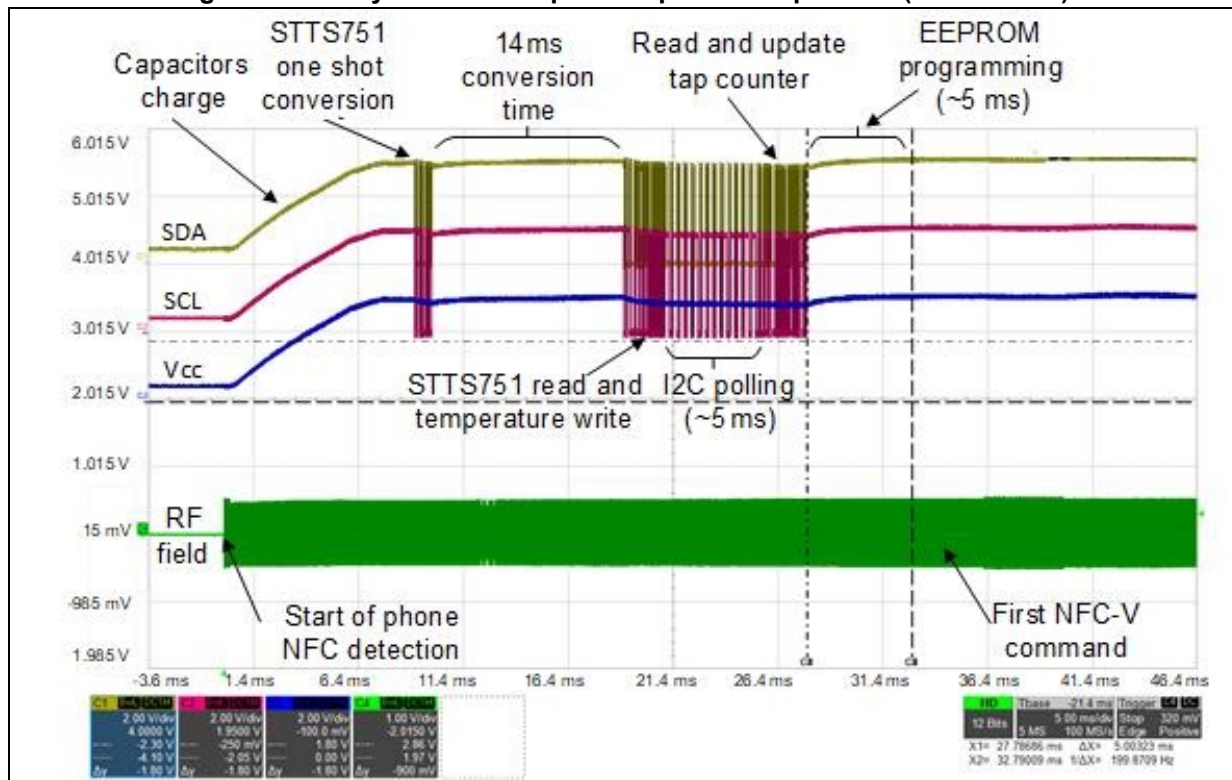
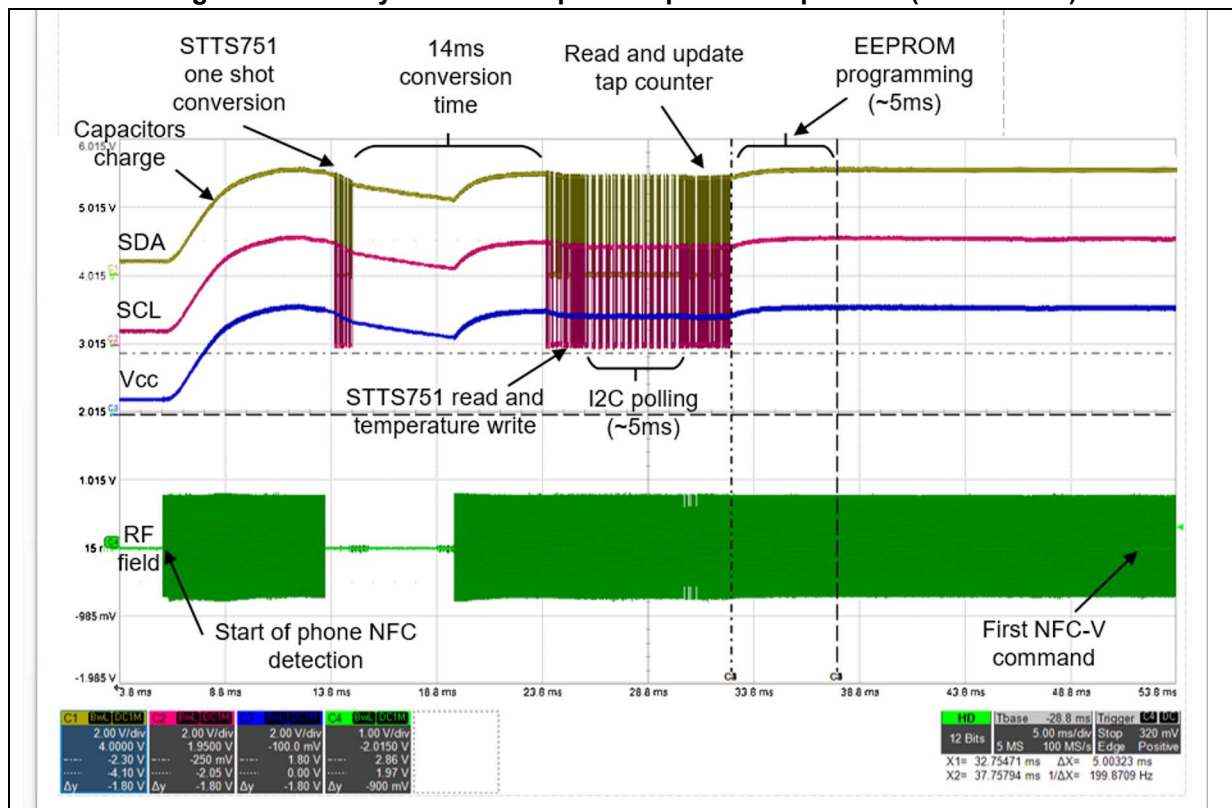


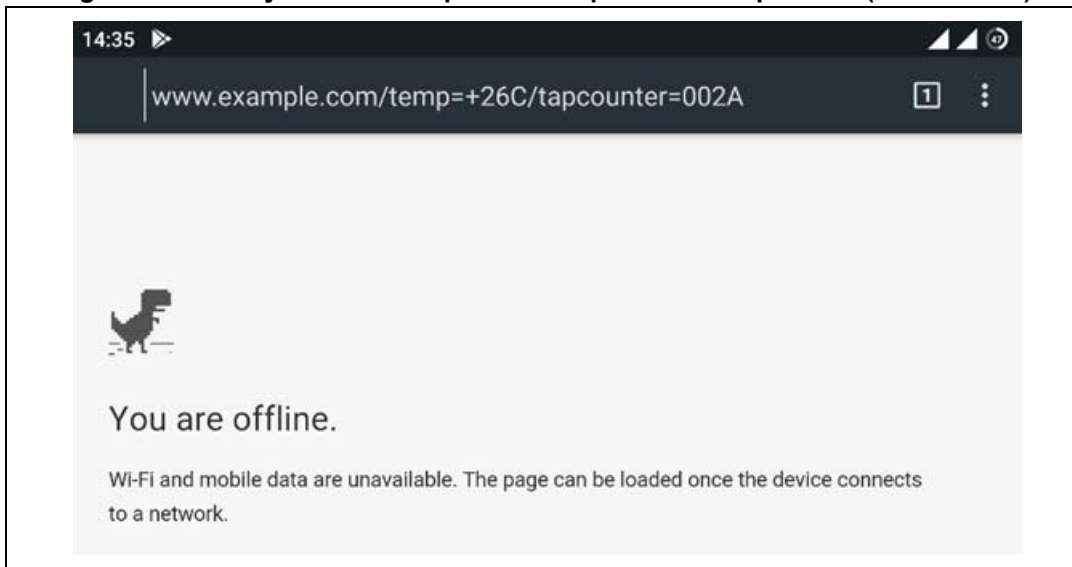
Figure 10. Battery-less NDEF update capture with phone 4 (ST25DV04K)



With the phone 4, RF field goes off for ~6 ms after first ACM detection, but the $2 \times 4.7 \mu\text{F}$ capacitors are enough to maintain V_{cc} voltage above 1.8 V.

After presenting the smartphone on the tag's antenna, the smartphone automatically opens the web browser, with the URL containing dynamic information about temperature (+26 °C) and tap count (2Ah, 42 taps) as shown in [Figure 11](#).

Figure 11. Battery-less NDEF update example result on phone 4 (ST25DV04K)



Example of battery-less automatic NDEF content update with ST25DV04KC

The ST25DV04K can advantageously be replaced by a ST25DV04KC, as it can write 16 bytes from I2C in 5 ms, when the ST25DV04K in the same 5 ms can write only 4 bytes (assuming data are page aligned). This makes possible to update the NDEF message faster or to update more data.

The hardware setup is the same, only ST25DV04K is replaced by ST25DV04KC (pin to pin compatible).

The NDEF message is slightly changed to align data to be updated with ST25DV04KC pages (example.com/current_temp=0000/tc=0000). This makes possible to update the temperature value and the tap counter value in a single 5 ms, 16-byte write, compared to the two 5 ms, 4-byte writes needed by the ST25DV04K.

Temperature value and tap counter value are on same page (16 bytes, starting at address 0020h) and are updated in a single I2C write command.

Table 3. Tag memory content (ST25DV04KC)

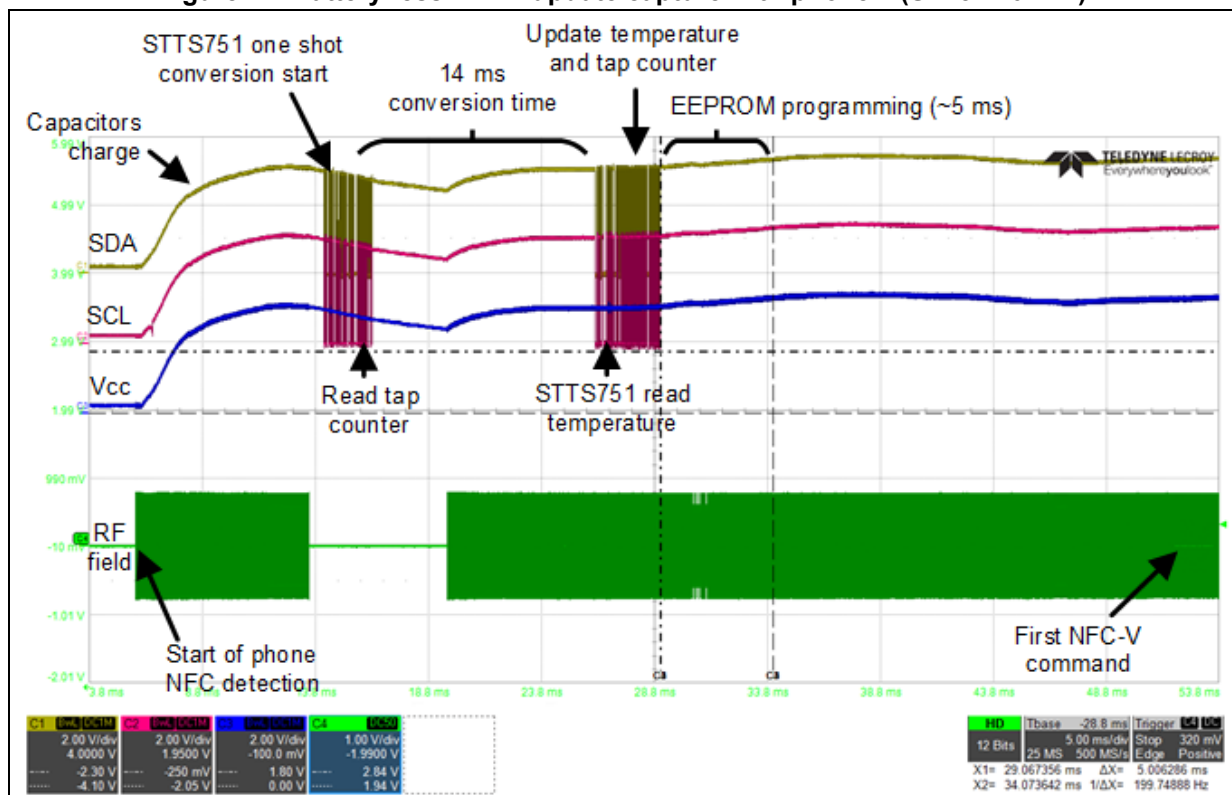
Byte address	Byte value	ASCII	Comment
0000	E1 40 40 00 03 2A D1 01 26 55 01 65 78 61 6D 70	á@@@..*Ñ.&U.examp	CCFile+TLV
0010	6C 65 2E 63 6F 6D 2F 63 75 72 72 65 6E 74 5F 74	le.com/current_t	-
0020	65 6D 70 3D 30 30 30 30 2F 74 63 3D 30 30 30 30	emp=0000/tc=0000	Page to be updated
0030	FE 00 00 00 00 00 00 00 00 00 00 00 00 00 00 00	P.....	TLV terminator

Sample code executed by the microcontroller with ST25DV04KC:

```
/* initialize string to be written in NDEF */
char data_char[16] = "emp=0000/tc=0000";
/* initialize I2C bus and clocks */
I2C_Init();
/* Launch sensor acquisition */
OneShotTemperature ();
/* read current tap counter in tag's EEPROM (4Bytes) */
I2C_ReadBuffer(ST25DV_ADDRESS_USER, 0x002C, 4, data_char+12);
/* wait for sensor to complete acquisition */
Delay(14ms);
/* Read I2C sensor to get current temperature */
ReadOneTemperature (&data_sensor);
/* convert temperature value to ASCII */
ConvertTempToAscii(data_sensor, data_char+4);
/* increment tap counter value in ASCII */
IncrementTapCounterAscii(data_char+12);
/* update temperature and tap counter values in NDEF message (16 bytes) */
I2C_WriteOnePage(ST25DV_ADDRESS_USER, 0x0020, data_char);
/* immediately stop MCU to reduce power consumption */
halt();
```

Figure 12 is an oscilloscope screenshot showing the NDEF update in action on phone 4.

Figure 12. Battery-less NDEF update capture with phone 4 (ST25DV04KC)



The ST25DV04KC provides additional timing margin between end of NDEF update in EEPROM and first NFC-V command.

2.1.5 Battery powered automatic NDEF content update implementation

When timing constraint of 30 ms is not achievable, another method allowing longer time to update the NDEF message is possible.

As seen in [Section 2.1.2](#), smartphones are continuously polling for tags presence by sending short RF field bursts. This method makes use of capacity of ST25DV-I2C to detect those RF field bursts to trigger the NDEF update. Once NDEF is updated, the ST25DV-I2C is configured to answer normally to the next smartphone polling sequence, until the NDEF message is read. This creates a small delay in answer when a smartphone taps the tag, but it is limited to 500 ms or less with most smartphones.

Since there is no RF field between two polling sequences, energy harvesting cannot be used with this method the ST25DV-I2C and the microcontroller must be externally powered.

In principle, this augmented NDEF application:

- Behaves as a standard NFC tag
- Wakes-up the microcontroller on RF events
- Uses a battery or permanent supply to power the microcontroller and other possible on board external devices
- On first RF field rising, updates NDEF message. The battery power allows NDEF update even when RF field is off
- On next RF field rising, waits for NDEF read from the smartphone.
- After detection of NDEF read by the smartphone, waits for the next RF field rising to update the NDEF again
- The initial NDEF message is first programmed into ST25DV-I2C memory

This augmented NDEF method is based on RF events detection. The application must detect a RF field rising event, and an NDEF message read.

The RF field rising detection is performed using the ST25DV-I2C RF_FIELD_RISING event detection.

The NDEF message read can be interpreted by combining two event detections: RF_ACTIVITY and RF_FIELD_FALLING. The smartphone finishes reading the NDEF message if RF activity has been detected and the RF field goes off (meaning the smartphone has been removed).

A global variable is used as a flag to keep trace if NDEF update has already been done:

- Upon detection of RF field rising, the microcontroller checks this variable to know if NDEF update must be done or not. If flag is not set, NDEF update is done and the flag is set.
- Upon detection of RF activity and RF field falling, the microcontroller checks this flag to know if NDEF update has previously been achieved. If yes, NDEF message is considered read and the flag is unset.

During NDEF update, the ST25DV-I2C is set in RF_SLEEP mode so that any incoming RF command is just ignored. This provides two benefits:

- Prevents any false or partial detection of the tag by the smartphone during the NDEF update

- Prevents any RF perturbation during I2C access (I2C accesses are not blocked by any RF access)

With this method, it is not required to implement any anti-tearing technique as, for the battery-less method, there is not risk of tearing (the ST25DV-I2C is continuously powered by the battery during EEPROM programming).

Figure 13 and Figure 14 summarize the complete NDEF update sequence:

Figure 13. Battery powered NDEF update chronogram (1/2)

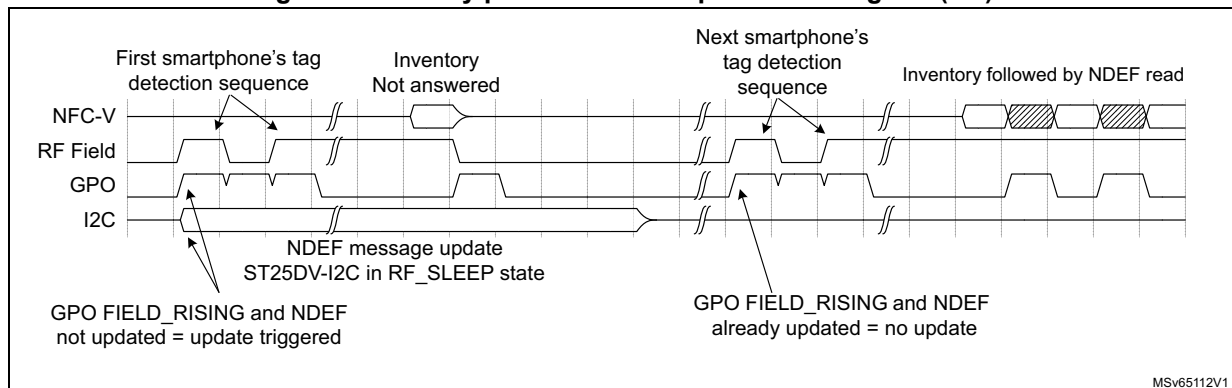
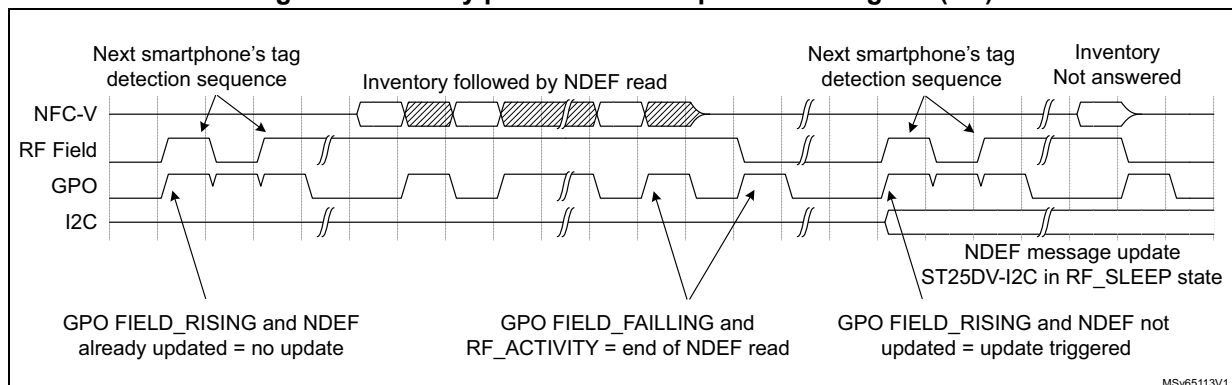


Figure 14. Battery powered NDEF update chronogram (2/2)



Example of battery powered automatic NDEF content update implementation

In this example the augmented NDEF tag provides an NDEF message that contains an SMS. The message is automatically updated with the tag UID, three sensors' values and a tap counter incremented at each NDEF read.

Hardware setup:

- A X-NUCLEO-NFC05A1 shield, embedding a ST25DV04K dynamic tag, with NDEF message preloaded
- A NUCLEO-L053R8 board, embedding a STM32L053 microcontroller

ST25DV-I2C memory is preloaded with the NDEF message, with sensors and tap counter values set to 0.

Sample of code executed by the microcontroller:

```
/* Init ST25DV driver */
while( NFC04A1_NFCTAG_Init(NFC04A1_NFCTAG_INSTANCE) != NFCTAG_OK );
```

```

/* Set EXTI settings for GPO Interrupt */
NFC04A1_GPO_Init();
/* Set GPO Configuration: RF Field change and RF activity */
NFC04A1_NFCTAG_ConfigIT(NFC04A1_NFCTAG_INSTANCE, ST25DV_GPO_ENABLE_MASK |
ST25DV_GPO_FIELDCHANGE_MASK | ST25DV_GPO_RFACTIVITY_MASK);

/* main loop */
while(1)
{
    if( GPOActivated == 1 )
    {
        /* Read ITSTS_Dyn to determine source of the GPO interrupt */
        NFC04A1_NFCTAG_ReadITSTStatus_Dyn(NFC04A1_NFCTAG_INSTANCE, &ItStatus )
;
        switch( ItStatus )
        {
            case ST25DV_ITSTS_DYN_FIELDRISING_MASK:
            case ST25DV_ITSTS_DYN_FIELDRISING_MASK |
ST25DV_ITSTS_DYN_FIELDFALLING_MASK:
            case ST25DV_ITSTS_DYN_FIELDRISING_MASK |
ST25DV_ITSTS_DYN_RFACTIVITY_MASK:
                /* RF field rising detected */
                if( NDEF_update_done == 0) /* update to be done ? */
                {
                    /* set ST25DV in RF_SLEEP mode */
                    passwd.MsbPasswd = 0; passwd.LsbPasswd = 0;
                    NFC04A1_NFCTAG_PresentI2CPassword(NFC04A1_NFCTAG_INSTANCE, passwd
);

                    NFC04A1_NFCTAG_SetRFSleep( NFC04A1_NFCTAG_INSTANCE );
                    /* update NDEF content */
                    MX_NFC4_NDEFUpdate();
                    NDEF_update_done = 1;
                    /* exit ST25DV from RF_SLEEP mode */
                    NFC04A1_NFCTAG_ResetRFSleep( NFC04A1_NFCTAG_INSTANCE );
                    passwd.MsbPasswd = 123; passwd.LsbPasswd = 456;
                    NFC04A1_NFCTAG_PresentI2CPassword(NFC04A1_NFCTAG_INSTANCE, passwd
);

                }
                break;
            case ST25DV_ITSTS_DYN_FIELDFALLING_MASK |
ST25DV_ITSTS_DYN_RFACTIVITY_MASK:
            case ST25DV_ITSTS_DYN_FIELDRISING_MASK |
ST25DV_ITSTS_DYN_FIELDFALLING_MASK | ST25DV_ITSTS_DYN_RFACTIVITY_MASK:
                /* RF activity and RF field falling detected */
                if( NDEF_update_done == 1) /* update already done ? */
                {
                    /* NDEF has been read, next RF field rising: update to be done */

```

```
        NDEF_update_done = 0;
    }
    break;
case ST25DV_ITSTS_DYN_RFACTIVITY_MASK:
case ST25DV_ITSTS_DYN_FIELDFALLING_MASK:
default:
    break;
}
GPOActivated = 0;
}
}

/* call back function from IT */
void BSP_GPO_Callback(void)
{
    GPOActivated = 1;
}
```

The STM32L0 Series is configured so that the GPO interruption sets the GPOActivated global variable to 1. The main loop is polling on this variable value change to start the NDEF update process. The first step is to read the ITSTS_Dyn status register to check the nature of the RF event. Then, depending on the RF event and on the value of NDEF_update_done global variable, decision is made to update or not the NDEF message.

[Figure 15](#) and [Figure 16](#) are logic analyzer screenshots showing the NDEF update in action on phone 4.

Figure 15. Battery powered NDEF update capture with phone 4 (NDEF update phase)

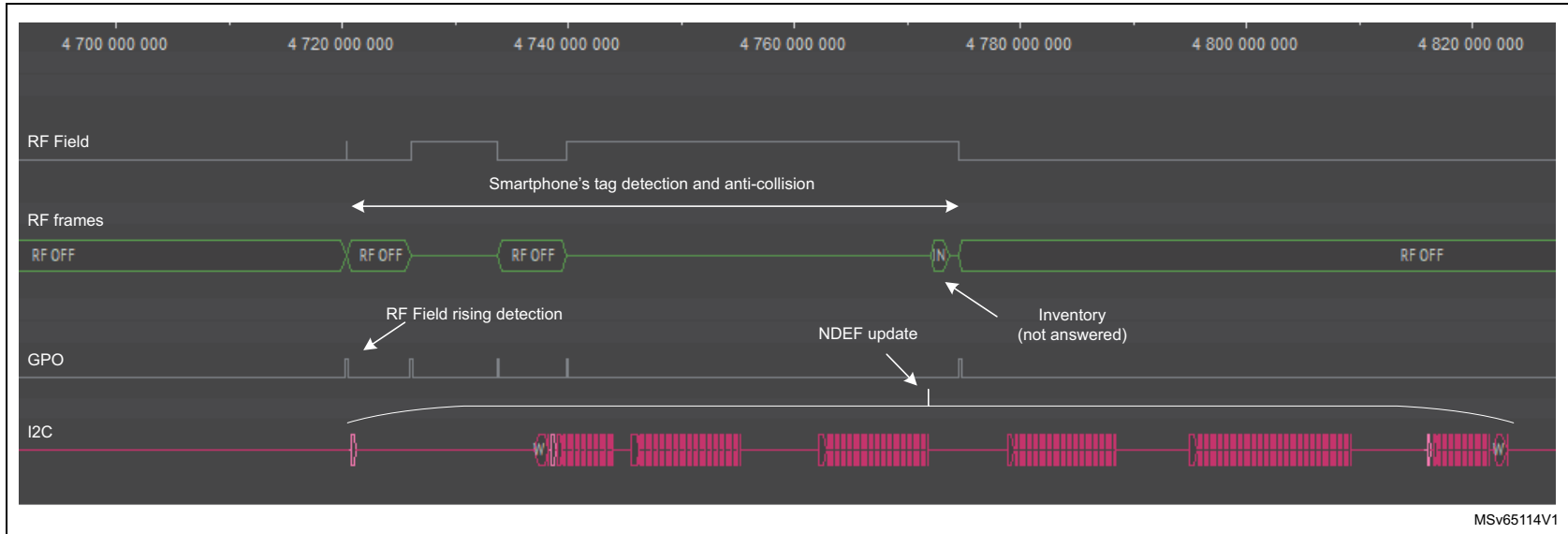
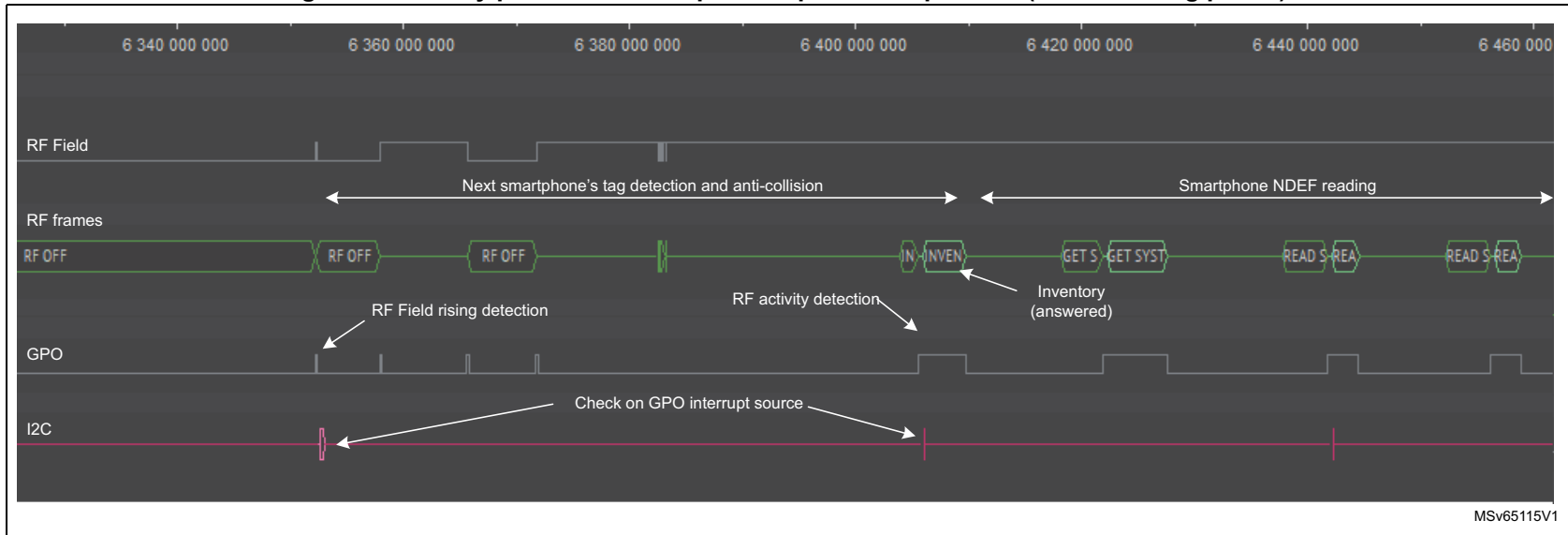
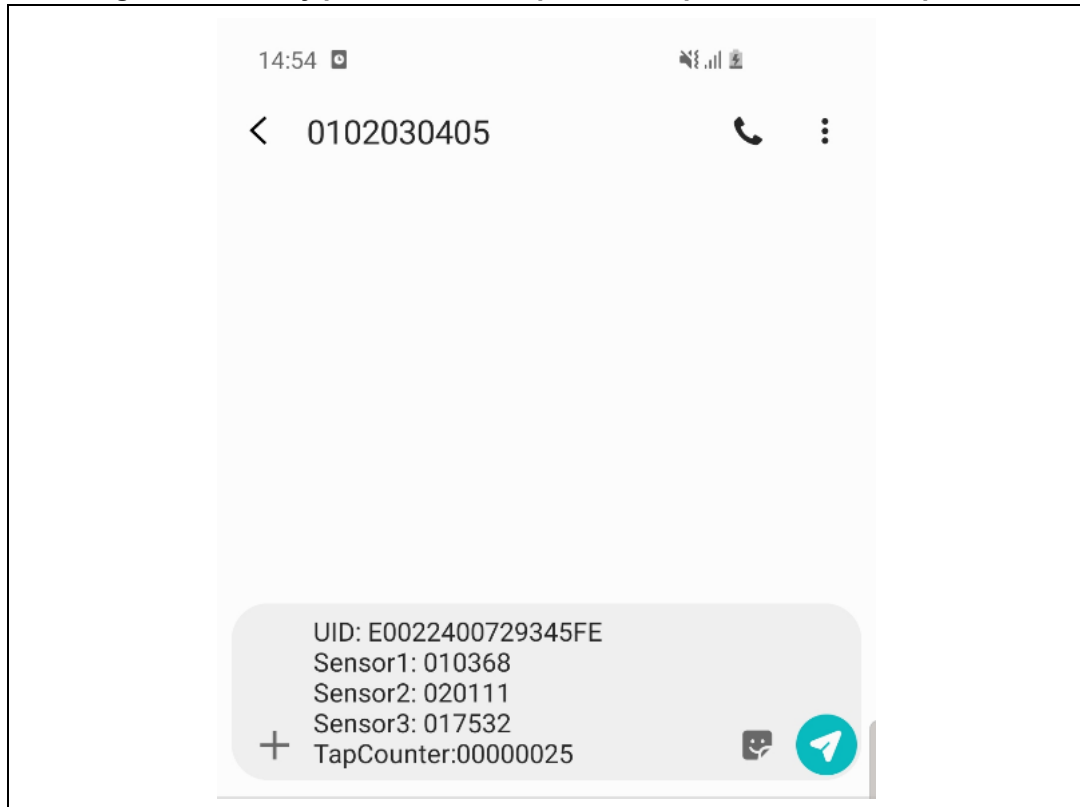


Figure 16. Battery powered NDEF update capture with phone 4 (NDEF reading phase)



After presenting the smartphone on the tag's antenna, the smartphone automatically opens the messaging application, with the SMS containing tag's UID, up-to-date sensors value and the tap count as shown in [Figure 17](#).

Figure 17. Battery powered NDEF update example result on smartphone



2.2 Periodical NDEF content update and update based on external events

If NDEF update cannot be done dynamically and synchronously to the smartphone presence detection, it can then be done asynchronously.

In this case, the NDEF message content is update periodically, or on other external events, independently of any RF activity. This is the case for example if you want to update NDEF content each time an alarm is triggered in the application, or in case the NDEF message is used as a data log.

As I2C and RF accesses are asynchronous in this method, the microcontroller and the smartphone try to access the ST25DV-I2C at the same time, which is not recommended. To avoid any possible conflict between I2C and RF, it is recommended to set the ST25DV-I2C in RF_SLEEP mode during update of the NDEF message content.

This method does not require any specific techniques, and therefore is not analyzed in this application note.

2.3 Configuration data considerations

A good practice is to store application configuration data into the NFC EEPROM rather than in the microcontroller Flash memory.

The advantage of storing settings (such as, sensors enabled, sampling period) in the EEPROM is that an NFC reader can directly read and write them, even if the application is not powered.

In case of augmented NDEF, all the dynamic NDEF parameters are stored into the ST25DV-I2C memory (such as, information and addresses to update inside the NDEF message). The reader can then update the NDEF message body and the addresses of bytes always updated dynamically at the same time. The microcontroller reads those configuration bytes before updating the NDEF message.

This is performed by defining two areas in ST25DV-I2C user memory, with area 0 always containing the CC File and the NDEF message, and area 1 containing the configuration data. Both areas can be protected independently, with different passwords if required.

3 Revision history

Table 4. Document revision history

Date	Revision	Changes
10-Apr-2020	1	Initial release.
28-Apr-2020	2	Updated Section 2.1: Automatic NDEF content update on phone detection .
05-May-2021	3	Updated Introduction , Section 2.1.3: Timing constraints for automatic NDEF content update , Section 2.1.4: Battery-less automatic NDEF content update implementation and Example of battery-less automatic NDEF content update with ST25DV04K . Updated Table 2: Tag memory content (ST25DV04K) . Added Example of battery-less automatic NDEF content update with ST25DV04KC . Minor text edits across the whole document.

IMPORTANT NOTICE – PLEASE READ CAREFULLY

STMicroelectronics NV and its subsidiaries (“ST”) reserve the right to make changes, corrections, enhancements, modifications, and improvements to ST products and/or to this document at any time without notice. Purchasers should obtain the latest relevant information on ST products before placing orders. ST products are sold pursuant to ST’s terms and conditions of sale in place at the time of order acknowledgement.

Purchasers are solely responsible for the choice, selection, and use of ST products and ST assumes no liability for application assistance or the design of Purchasers’ products.

No license, express or implied, to any intellectual property right is granted by ST herein.

Resale of ST products with provisions different from the information set forth herein shall void any warranty granted by ST for such product.

ST and the ST logo are trademarks of ST. For additional information about ST trademarks, please refer to www.st.com/trademarks. All other product or service names are the property of their respective owners.

Information in this document supersedes and replaces information previously supplied in any prior versions of this document.

© 2021 STMicroelectronics – All rights reserved